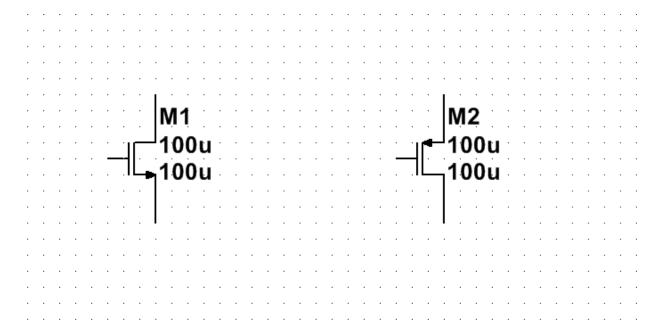
## **ECEN 326**

## **MOSFET Custom Models**

Instructor: Sam Palermo

The custom MOSFET models allow the flexibility to edit key device parameters ( $V_{TN/P}$ ,  $KP_{N/P}$ ,  $\lambda$ , W, L etc...) and also provides a more standard symbol. These use of these models may also help your matching between simulation and measurements. For both the NMOS and PMOS models, the body terminal is shorted to the source. Thus, it is only a 3-terminal model.



The custom MOSFET models are available for download from the class website in the Lab Section.

https://people.engr.tamu.edu/spalermo/ecen325/UsrComp S ECEN.usr

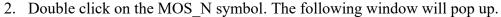
In order to use the custom models, follow the procedure outlined on Page 3 of the MultiSim and Analog Discovery 2 Manual.

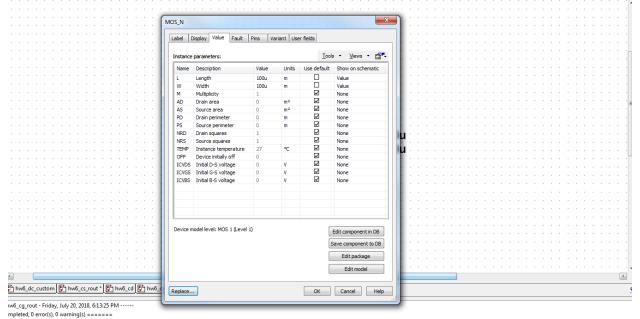
https://people.engr.tamu.edu/spalermo/ecen325/MultiSim-AnalogDiscovery2-Keysight-Manual.pdf

## **Using Custom NMOS to Mimic 2N7000 Example**

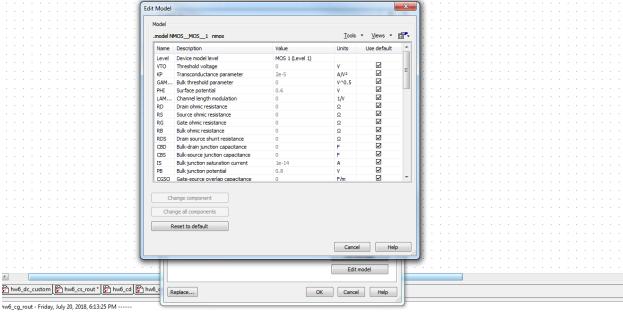
The default 2N7000 NMOS transistor model has a  $\beta$ =102mA/V<sup>2</sup> and V<sub>TN</sub>=2.0V. This can be emulated with the custom "MOS N" model with the following steps.

1. Place the MOS N model in your schematic.



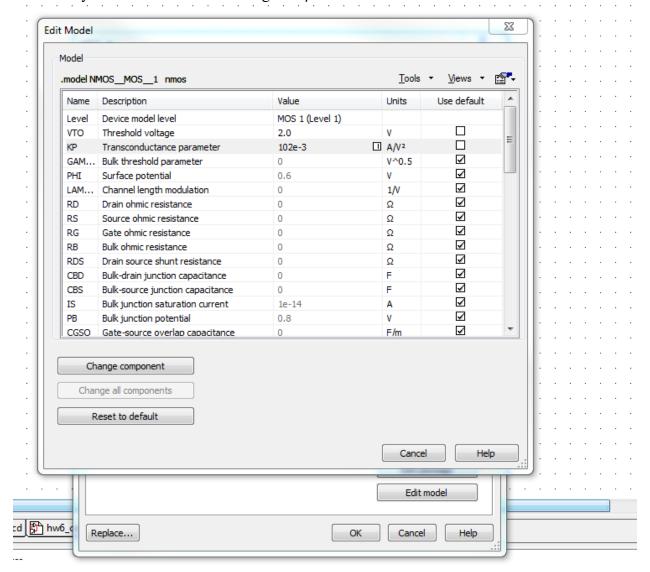


3. Click on Edit model. Another window will pop up.



impleted, 0 error(s), 0 warning(s) ======

4. To edit the transistor parameters, unclick the "Use default" box and edit the value in the "Value" field. Below is an example to emulate the default 2N7000 NMOS transistor model, with  $\beta$ =102mA/V<sup>2</sup> and V<sub>TN</sub>=2.0V. As the custom model has a default W/L=1, only the KP<sub>N</sub> value is edited to give a  $\beta$ =102mA/V<sup>2</sup>.



5. To commit these changes, click on "Change component". The transistor parameter window will disappear. Then click on "OK" and you will be back in your main schematic.

You can use a similar procedure for the PMOS device and other MOSFET transistors.